Compound Semiconductor Materials Japan TC Chapter

Meeting Summary and Minutes

In Conjunction with SEMICON Japan 2025
Thursday, December 18, 2025 14:00 – 16:00 JST
Room 907, TFT Building East Wing 9F, Tokyo, Japan/ Official Virtual TC Chapter Meeting (Hybrid)

TC Chapter Announcements

Next TC Chapter Meeting

TBD

Table 1 Meeting Attendees

Italics indicate virtual participants

Co-Chairs: Masayoshi Obara (Shin-Etsu Handotai)
SEMI Staff: Akiko Yoshida (SEMI Japan)

Company	*Last*	*First*	*Company*	*Last*	*First*
AIST	Senzaki	Junji	Self	Kitabatake	Makoto
CERTIE	*Ko*	*Kennis*	Self	Yoshise	Masanori
JX Advanced Metals	Hanzawa	Masaya	SOL	Takano	Tomonobu
Lasertec	Fujiki	Shota	Shin-Etsu Handotai	Obara	Masayoshi
Lasertec	Yamamoto	Mari	SiC Alliance	Toda	Kenji
Mitsubishi Electric	Iwamatsu	Toshiaki			
Nidek	Kondo	Toshiyuki	SEMI HQ	Nguyen	Kevin
Resonac	*Matsuse*	*Akihiro*	SEMI Japan	Yoshida	Akiko

Table 2 Leadership Changes

WG/TF/SC/TC Name	*Previous Leader*	*New Leader*
Compound Semiconductor Materials Japan TC Chapter	N/A	Makoto Kitabatake (Self)
SiC Material and Wafer Task Force	N/A	Masayoshi Obara (Shin-Etsu Handotai) Makoto Kitabatake (Self)

Table 3 TC Chapter Structure Changes

Previous WG/TF/SC Name	*New WG/TF/SC Name or Status Change*
Silicon Carbide Substrate Liaison TF	Disbanded
Silicon Epitaxial Wafer Liaison TF	Disbanded
SiC Material and Wafer Task Force	Newly formed

Table 4 Ballot Results

Document #	*Document Title*	*Committee Action*
None		

#1 **Passed** ballots and line items will be submitted to the ISC Audit & Review Subcommittee for procedural review.

#2 **Failed** ballots and line items were returned to the originating task forces for re-work and re-balloting or abandoning.

Table 5 Ratification Ballot Results

Document #	*Document Title*	*ISC A&R Action*	*A&R Forms*
None			

#1: **Passed** Ratification ballots will be submitted to SEMI publication for final processing.

#2: **Failed** Ratification ballots were returned to the originating task forces for re-work and re-balloting or abandoning.

Table 6 Activities Approved by the GCS between meetings of the TC Chapter

#	*Type*	*SC/TF/WG*	*Details*
None			

Table 7 Authorized Activities

Listing of all revised or new SNARF(s) approved by the Originating TC Chapter.

#	*Type*	*SC/TF/WG*	*Details*
None			

#1 SNARFs and TFOFs are available for review on the SEMI Web site at:
http://downloads.semi.org/web/wstdsbal.nsf/TFOFSNARF

Table 8 Authorized Ballots

#	*When*	*TF*	*Details*
None			

Table 9 SNARF(s) Granted a One-Year Extension

#	*TF*	*Title*	*Expiration Date*
None			

Table 10 SNARF(s) Cancelled

#	*TF*	*Title*
None		

Table 11 Standard(s) to receive Inactive Status

Standard Designation	*Title*
None	

Table 12 New Action Items

Item #	*Assigned to*	*Details*
SW20251218-01	Masayoshi Obara (TC chair)	To recommend the JRSC to appoint Makoto Kitabatake as a co-chair of the Compound Semiconductor Materials Japan TC Chapter.

Table 13 Previous Meeting Action Items

Item #	*Assigned to*	*Details*
CSM_20250630-01	SEMI Staff	To forward ballot review results of Doc.#7211A to the ISC A&R SC for procedural review. →Closed
CSM_20250630-02	TC members	To discuss the remaining issues of SiC Epitaxial Wafer. →Closed

1 Welcome, Reminders, and Introductions

Masayoshi Obara (Shin-Etsu Handotai) called the meeting to order at 2:00 PM JST. The meeting reminders on antitrust issues, intellectual property issues and holding meetings with international attendance were reviewed. Attendees introduced themselves.

Attachment: 01_Meeting Reminders

2 Review of Previous Meeting Minutes

The TC Chapter reviewed the minutes of the previous meeting.

Motion:	Approve the minutes as written.
By / 2nd:	Junji Senzaki (AIST)/ Kenji Toda (SiC Alliance)
Discussion:	None.
Vote:	9-Y 0-N. Motion passed.

Attachment: 02_TC Minutes_20250630_R0

3 Technical Committee Awards

Technical Committee Award recognizes leadership in document development, committee management, task force coordination, and Standards dissemination. The following members received the awards for their outstanding leadership and active contributions:

- Makoto Kitabatake (Self)
- Masanori Yoshise (Self)

4 Liaison Reports

4.1 *Japan Regional Standards Committee (JRSC)*

Akiko Yoshida (SEMI Japan) reported for the JRSC the previous meeting was held on December 15, 2025. Topics that are relevant to the Compound Semiconductor Materials Japan TC Chapter were:

- To further promote awareness of individual contributions to standards activities, the JRSC took the following actions:
    - The JRSC revised the Award Guidelines for the “Technical Committee Award,” which recognizes individuals who have made outstanding contributions to respective TC in Japan Region. In the past,

the Guideline stated that, in principle, the same individual was not awarded multiple times for the same document or activity, even across different years. However, the revised Guideline now allows individuals to be recognized for their significant contributions in a given year, even if the same work continues for multiple years.

  - In the past, recipients of the Technical Committee Award were recognized during the TC meetings held in conjunction with SEMICON Japan or the subsequent nearest meeting, and the recognition was recorded in the meeting minutes. However, the JRSC decided that award recipients would also be featured on a display panel at the SEMICON Japan venue.

- The Planning Meeting was held on Thursday, August 28, inviting TF leaders as well as TC co-chairs to deepen knowledge related to standardization. This year's theme was "Gaps in Supply Chain Transparency and SEMI Standards."
- According to the report from the Compound Semiconductor Materials Japan TC Chapter, concerns were raised regarding the lack of transparent procedures at the previous China TC Chapter meeting. Specifically, it was noted that Chinese was used as the primary language even with international guests present, and the voting process lacked clarity due to limited access to SVM for members in China. The JRSC reviewed these issues and decided to await the outcome of the planned SVM improvements, which aim to provide all members in China with login access. These enhancements are expected to be implemented in February.

Attachment: 03_JRSC Report_October 2025_R0

4.2 *Global Coordinating Subcommittee (GCS)*

Akiko Yoshida (SEMI Japan) reported for the GCS that there was no GCS discussion or voting between Compound Materials Japan TC Chapter meetings.

4.3 *Compound Semiconductor Materials Europe TC Chapter*

Kevin Nguyen (SEMI HQ) reported for the Compound Semiconductor Materials Europe TC Chapter. Of note:

- Last meeting was held on November 20, 2025 in conjunction with SEMICON Europa, and the next meeting will be held in Spring, 2026 online.
- SNARF 7417, Line-Item Revision of M55-0921, Specification for Polished Monocrystalline Silicon Carbide Wafers, and SNARF 7416, Reapproval of M82-0820, Test Method for the Carbon Acceptor Concentration in Semi-Insulating Gallium Arsenide Single Crystals by Infrared Absorption Spectroscopy were approved.
- Doc.#7417, Line-Item Revision of M55-0921, Specification for Polished Monocrystalline Silicon Carbide Wafers, Doc.#7416, Reapproval of M82-0820, Test Method for the Carbon Acceptor Concentration in Semi-Insulating Gallium Arsenide Single Crystals by Infrared Absorption Spectroscopy and Doc.#7111, Revision of SEMI M81-0418, Guide to Defects Found in Monocrystalline Silicon Carbide Substrates will be submitted for Cycle 1 or 2, 2026.
- Project period of SNARF 7111 (Revision to SEMI M81) was extended to November 14, 2026.

Attachment: 04_EU CSM Liaison Report November 2025 2

4.4 *Compound Semiconductor Materials North America TC Chapter*

Kevin Nguyen (SEMI HQ) reported for the Compound Semiconductor Materials North America TC Chapter that there had been no updates from the previous meeting back in 2022.

4.5 *Compound Semiconductor Materials China TC Chapter*

Kevin Nguyen (SEMI HQ) reported for the Compound Semiconductor Materials China TC Chapter. Of note:

- Last meeting was held on October 22, 2025 and next meeting is TBD.

- SNARF 6767, New Standard: Test Method for GBIR, SBIR, GF3R, SFQR and SORI of Silicon Carbide Wafers by Oblique Incident Interference Method, and SNARF 6769, New Standard: Test Method for Residual Stress of Silicon Carbide Wafers by Photoelastic Effect were abolished.
- SNARF 7407, New Standard: Test method for determining net carrier density profiles in silicon carbide epitaxial wafers by capacitance-voltage measurements with a mercury probe, and SNARF, New Standard: Specification For Bonding Silicon Carbide Homoepitaxial Wafer were approved.

Attachment: 05_CSM China TC Chapter Dec 2025

5 SEMI Staff Report

Akiko Yoshida (SEMI Japan) gave the SEMI Staff Report. Of notes:

- At SEMICON West 2025, for the first time in Phoenix, Arizona in October, the second round of SEMI Global Standards Summit (GSS) was held in the afternoon on Tuesday, October 7. The GSS is a strategic forum dedicated to identifying standards-critical areas and advancing an industry-wide standardization roadmap for the next 3- and 7-year horizons. The theme was "Future Standards for Connected & Sustainable Semiconductor Manufacturing."
- As for upcoming NA Standards meetings 2026, NA Winter Meetings will be held in February in a full virtual format, NA Spring Meetings will be held in Albany, New York in May in conjunction with ASMC, and SEMICON West Meetings in October in San Francisco.
- SEMICON Japan 2025 taking place this week have irregular venue arrangements because of renovations at Tokyo Big Sight. Friendship party and awards ceremony will be held at TFT Building as well.

Attachment: 06_Staff Report_December 2025_R4

6 Ballot Review

None.

7 Subcommittee and Task Force Reports

7.1 *Silicon Carbide Substrate Liaison Task Force*

Masayoshi Obara (Shin-Etsu Handotai) reported that the Silicon Carbide Substrate TF had no recent activities but noted that the members of the Japan TC Chapter discussed changing its structure to facilitate future work in November.

Motion:	Disband the Silicon Carbide Substrate Liaison TF.
By / 2nd:	Makoto Kitabatake (Self)/ Junji Senzaki (AIST)
Discussion:	None.
Vote:	10-Y 0-N. Motion passed.

7.2 *SiC Epitaxial Wafer Liaison Task Force*

Masayoshi Obara (Shin-Etsu Handotai) reported that the SiC Epitaxial Wafer Liaison TF had no recent activities but noted that the members of the Japan TC Chapter discussed changing its structure to facilitate future work in November.

Motion:	Disband the SiC Epitaxial Wafer Liaison TF.
By / 2nd:	Makoto Kitabatake (Self)/ Junji Senzaki (AIST)
Discussion:	None.
Vote:	10-Y 0-N. Motion passed.

8 Old Business

8.1 *Project Period Review*

No SNARF will be expiring soon.

8.2 *5-Year Review*

No document is subject for 5-year review within this year.

9 New Business

9.1 *TFOF for SiC Material and Wafer Task Force*

Upon decision to disband two TFs, Makoto Kitabatake (Self) proposed establishing a new Task Force to enable more comprehensive activities and to take a proactive role in document development.

Motion:	Approve the TFOF for SiC Material and Wafer TF.
By / 2nd:	Makoto Kitabatake (Self)/ Kenji Toda (SiC Alliance)
Discussion:	None.
Vote:	9-Y 0-N. Motion passed.

Attachment: 07_TFOF for SiC Material and Wafer TF_1201-Kita-Masiro

9.2 *Leadership Change*

Masayoshi Obara (Shin-Etsu Handotai), who have been a TC chair for a long period of time, recommended Makoto Kitabatake (Self) to be a TC co-chair of the Compound Semiconductor Materials Japan TC Chapter.

Motion:	Propose to approve Makoto Kitabatake (Self) to be a co-chair of the Compound Semiconductor Materials Japan TC Chapter.
By / 2nd:	Kenji Toda (SiC Alliance)/ Junji Senzaki (SiC Alliance)
Discussion:	None.
Vote:	9-Y 0-N. Motion passed.

Based on the above approval, a recommendation will be made to the JRSC to appoint Makoto Kitabatake as a co-chair of the Compound Semiconductor Materials Japan TC Chapter.

Staff Note: The co-chairs are appointed by the responsible RSC per Regulations 5.7.5.

10 Action Item Review

10.1 *Open Action Item*

Item #	*Assigned to*	*Details*
CSM_20250630-01	SEMI Staff	To forward ballot review results of Doc.#7211A to the ISC A&R SC for procedural review. →Closed. Doc.#7211 is pending publication.
CSM_20250630-02	TC members	To discuss the remaining issues of SiC Epitaxial Wafer. →Closed. The discussion will be started under the new TF.

10.2 *New Action Item*

Item #	*Assigned to*	*Details*
SW20251218-01	Masayoshi Obara (TC chair)	To recommend the JRSC to appoint Makoto Kitabatake as a co-chair of the Compound Semiconductor Materials Japan TC Chapter.

11 Next Meeting and Adjournment

The next meeting is scheduled in the middle of Jun2, 2026 at SEMI Japan, Tokyo, Japan/ Official Virtual TC Chapter Meeting (Hybrid). Exact date and time is TBD. Refer to http://www.semi.org/standards-events for the current list of events.

Adjournment: 16:00.

Respectfully submitted by:

Akiko Yoshida
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SEMI Japan
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Email: ayoshida@semi.org

Minutes tentatively approved by:

Masayoshi Obara (Shin-Etsu Handotai), Co-chair	January 9, 2026

Table 14 Index of Available Attachments[#1]

Title	*Title*
01_Meeting Reminders	05_CSM China TC Chapter Dec 2025
02_TC Minutes_20250630_R0	06_Staff Report_December 2025_R4
03_JRSC Report_October 2025_R0	07_TFOF for SiC Material and Wafer TF_1201-Kita-Masiro
04_EU CSM Liaison Report November 2025 2	

#1 Due to file size and delivery issues, attachments must be downloaded separately. A .zip file containing all attachments for these minutes is available at www.semi.org. For additional information or to obtain individual attachments, please contact Akiko Yoshida at the contact information above.